

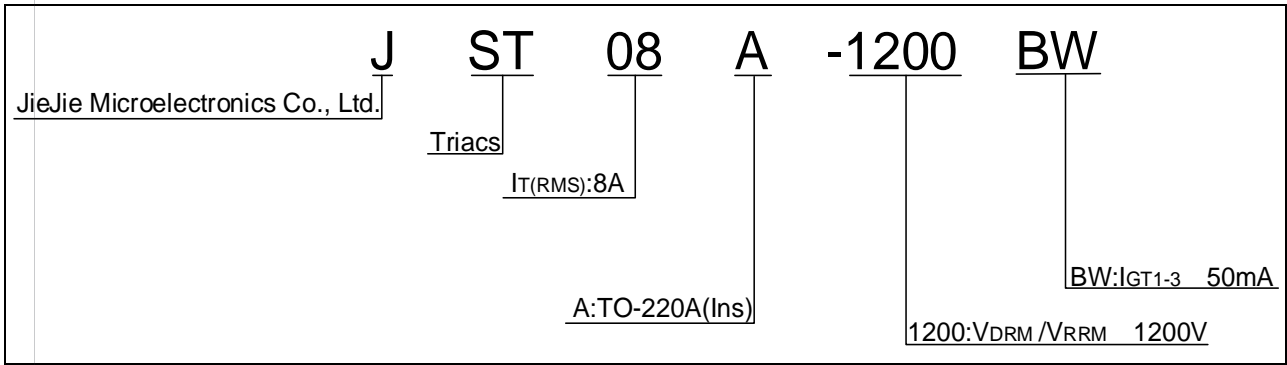
| | | | |
|--|----------|-----|----|
| Peak gate power | P_{GM} | 10 | W |
| Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7) | V_{pp} | 2.5 | kV |

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

| Symbol | Test Condition | Quadrant | Value | | Unit |
|----------|---------------------------------------|----------|-------|-----|------|
| I_{GT} | $V_D=12V$ $R_L=33$ | - - | MAX. | 50 | mA |
| V_{GT} | | - - | MAX. | 1 | V |
| V_{GD} | $V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$ | - - | MIN. | 0.2 | V |

$$I_L = 1.2I_{GT}$$

ORDERING INFORMATION



MARKING

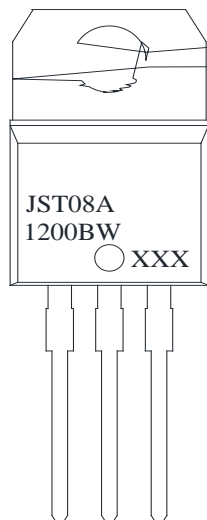


FIG.1: Maximum power dissipation versus RMS
on-state i_e

ORDERING INFORMATION

| Order code | Voltage V_{DRM}/V_{RRM} (V) | IGT(mA) | Package | Base qty. (pcs) | Delivery RMRRM |
|------------|----------------------------------|---------|---------|--------------------|---|
|------------|----------------------------------|---------|---------|--------------------|---|

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